

# **Dual SPDT Analog Switch**

#### **DESCRIPTION**

The DG9636 is a CMOS, dual SPDT analog switch designed to operate from 2.7 V to 12 V, single supply. All control logic inputs have a guaranteed 1.65 V logic HIGH threshold when operation from a 12 V power supply. This makes the DG9636 ideally suited to interface directly with low voltage micro-processor control signals.

Processed with high density CMOS technology, the DG9636 has a 83  $\Omega$  channel ON resistance while providing ultra low parasitic capacitance of 2 pF for CS<sub>(off)</sub> and 7 pF for CD<sub>(on)</sub>. Other performance features are: 720 MHz -3 dB bandwidth, -67 dB Cross Talk and -58 dB Off isolation at 10 MHz frequency.

Key applications for the DG9636 are logic level translation, pulse generator, and high speed or low noise signal switching in precision instrumentations and portable device designs.

The DG9636 is available in space saving 1.4 mm x 1.8 mm miniQFN10 package.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL rating.

#### **FEATURES**

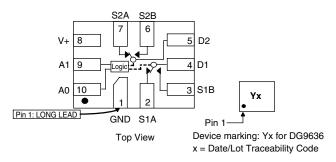
- Leakage current < 0.5 nA max. at 85 °C
- Low switch capacitance (C<sub>soff</sub>, 2 pF typ.)
- R<sub>DS(on)</sub> -83 Ω max.
- Low voltage, 1.65 V CMOS/TTL compatible
- 720 MHz, -3 dB bandwidth
- Fully specified with single supply operation at 12 V
- Excellent isolation and crosstalk performance (typ. > -60 dB at 10 MHz)
- Fully specified from -40 °C to 85 °C and -40 °C to +125 °C
- Latch-up current 300 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: For definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **APPLICATIONS**

- · High-end data acquisition
- Medical instruments
- · Precision instruments
- High speed communications applications
- Automated test equipment
- · Sample and hold applications

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**

#### DG9636 miniQFN - 10L



TRUTH TABLE	TRUTH TABLE									
Selec	cted Input	On Switches								
A1	A0	DG9636								
X	0	D1 to S1A								
X	1	D1 to S1B								
0	X	D2 to S2A								
1	X	D2 to S2B								





ORDERING INFORMATION								
Temp. Range	Part Number							
-40 °C to 125 °C	10 pin miniQFN	DG9636EN-T1-E4						
-40 °C to 85 °C	10 pin miniQFN	DG9636DN-T1-E4						

#### Note

• -40 °C to 85 °C datasheet limits apply.

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)									
Parameter	Limit	Unit							
V+ to GND		14	V						
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V+) +0.3 or 30 mA, whichever occurs first	V						
Continuous Current (Any Terminal)		30	mA						
Peak Current, S or D (Pulsed 1 ms, 10 % Duty	Cycle)	100	IIIA						
Storage Temperature		-65 to 150	°C						
Power Dissipation (Package) b	10 pin miniQFN c, d	208	mW						
Thermal Resistance (Package) <sup>b</sup>	357	°C/W							

#### **Notes**

- a. Signals on SX, DX, or AX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.
- d. Manual soldering with iron is not recommended for leadless components. The miniQFN-10 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS										
_		Test Conditions		_	-40 °C t	o 125 °C	-40 °C to 85 °C			
Parameter	Symbol	Unless Otherwise Specified $V+ = 12 \text{ V}, V_{A0, A1} = 1.65 \text{ V}, 0.5 \text{ V}^a$	Temp. b Typ. c		Min. d	Max. d	Min. d	Max. d	Unit	
Analog Switch										
Analog Signal Range e	V <sub>ANALOG</sub>		Full	ı	-	12	ı	12	>	
On-Resistance	Basis	$I_S = 1 \text{ mA}, V_D = +11.3 \text{ V}$	Room	83	-	110	ı	110		
OII-I lesistarice	R <sub>DS(on)</sub>	ig = 1 111A, VD = +11.5 V	Full	1	-	140	ı	125		
On-Resistance Match	AD	I <sub>S</sub> = 1 mA, V <sub>D</sub> = +11.3 V	Room	2	-	4	-	4	Ω	
On-nesistance Match	$\Delta R_{on}$	$I_S = I IIIA, V_D = +II.3 V$	Full	-	-	9	-	6	2.2	
On-Resistance Flatness	В	I <sub>S</sub> = 1 mA, V <sub>D</sub> = 0.7 V, 6.5 V, 11.3 V	Room	33	=.	45	-	45		
On-nesistance riathess	R <sub>FLATNESS</sub>	$I_S = I IIIA, V_D = 0.7 V, 0.3 V, II.3 V$	Full	-	-	55	-	50		
			Room	± 0.01	-1	1	-1	1		
Switch Off	I <sub>S(off)</sub>	V+ = 12 V,	Full	-	-18	18	-2	2		
Leakage Current	,	$V_D = 1 \text{ V/11 V}, V_S = 11 \text{ V/1 V}$	Room	± 0.01	-1	1	-1	1	<b></b> Λ	
	I <sub>D(off)</sub>		Full	-	-18	18	-2	2	nA	
Channel On		V+ = 12 V,	Room	± 0.01	-1	1	-1	1		
Leakage Current	I <sub>D(on)</sub>	$V_D = V_S 11 V/1 V$	Full	-	-18	18	-2	2		
Digital Control										
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>AX</sub> = 0.5 V	Full	0.005	-0.1	0.1	-0.1	0.1		
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>AX</sub> = 1.65 V	Full	0.005	-0.1	0.1	-0.1	0.1	μA	
Input Capacitance e	C <sub>IN</sub>	f = 1 MHz	Room	3	-	-	ı	-	pF	

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SPECIFICATIONS									
_		Test Conditions			-40 °C to 125 °C		-40 °C to 85 °C		
Parameter	Symbol	Unless Otherwise Specified $V+ = 12 \text{ V}, V_{A0, A1} = 1.65 \text{ V}, 0.5 \text{ V}^a$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. d	Max. d	Min. d	Max. d	Unit
Dynamic Characteristic	s								
Turn-On Time	ton		Room	30	-	70	ı	70	
rum-on nine	ton		Full	-	-	90	ı	80	
Turn-Off Time	t <sub>off</sub>	$R_L = 300 \Omega, C_L = 35 pF$	Room	15	-	55	-	55	ns
rum-on nine	Loff	see figure 1, 2	Full	-	-	75	ı	65	115
Break-Before-Make	+		Room	15	5	-	5	-	
Dieak-Deloie-Wake	t <sub>BBM</sub>		Full	-	2	-	2	-	
Charge Injection e	$Q_{INJ}$	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	23.5	-	-	-	-	рC
Off Isolation e	OIRR	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	Room	-58	-	-	-	-	dB
Bandwidth <sup>e</sup>	BW	$R_L = 50 \Omega$	Room	720	-	-	-	-	MHz
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	Room	-67	-	-	-	-	dB
Dynamic Characteristic	s								
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>	f = 1 MHz	Room	2	-	-	-	-	~F
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	I = I WINZ	Room	7.7	-	-	-	-	pF
Total Harmonic Distortion <sup>e</sup>	THD	Signal = 1 $V_{RMS}$ , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	0.01	-	-	-	-	%
Power Supplies									
Dower Cumply Current	l+		Room	0.001		0.5	-	0.5	
Power Supply Current	I+	$V_{IN} = 0 \text{ V, or V+}$	Full	-	-	1	-	1	
Cround Current		v <sub>IN</sub> = 0 v, or v+	Room	-0.001	-0.5	-	-0.5	-	μA
Ground Current	I <sub>GND</sub>		Full	-	-1	-	-1	-	

SPECIFICATIONS	SPECIFICATIONS											
_		Test Conditions	_		-40 °C t	o 125 °C	-40 °C to 85 °C					
Parameter	Symbol	Unless Otherwise Specified $V+ = 5 V$ , $V_{A0, A1} = 1.4 V$ , $0.5 V$ a	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. d	Max. d	Min. d	Max. d	Unit			
Analog Switch												
Analog Signal Range e	V <sub>ANALOG</sub>		Full	-	-	5	-	5	V			
On-Resistance	В		Room	120	-	170	-	170				
On-nesistance	R <sub>DS(on)</sub>	$I_S = 1 \text{ mA}, V_D = +3.5 \text{ V}$	Full	-	-	250	-	200	Ω			
On-Resistance Match	$\Delta R_{on}$	$I_S = I IIIA, V_D = +3.5 V$	Room	3	-	5	-	5				
			Full	-	-	12	-	10				
	I <sub>S(off)</sub>		Room	± 0.01	-1	1	-1	1				
Switch Off		$V_{+} = 5.5 \text{ V},$ $V_{D} = 1 \text{ V}/4.5 \text{ V}, V_{S} = 4.5 \text{ V}/1 \text{ V}$	Full	-	-18	18	-2	2				
Leakage Current			Room	± 0.01	-1	1	-1	1	nA			
	I <sub>D(off)</sub>		Full	-	-18	18	-2	2	nA			
Channel On		V. 55VV V 4V/45V	Room	± 0.01	-1	1	-1	1				
Leakage Current	I <sub>D(on)</sub>	$V+ = 5.5 \text{ V}, V_S = V_D = 1 \text{ V}/4.5 \text{ V}$	Full	-	-18	18	-2	2				
Digital Control	Digital Control											
Input Current, V <sub>IN</sub> Low	IL	V <sub>AX</sub> = 0.5 V	Full	0.005	-0.1	0.1	-0.1	0.1				
Input Current, V <sub>IN</sub> High	I <sub>H</sub>	V <sub>AX</sub> = 1.4 V	Full	0.005	-0.1	0.1	-0.1	0.1	μA			
Input Capacitance	C <sub>IN</sub>	f = 1 MHz	Room	3	-	-	-	-	pF			

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SPECIFICATIONS									
		Test Conditions	<b>-</b> b		-40 °C to 125 °C		-40 °C to 85 °C		
Parameter	Symbol	Unless Otherwise Specified $V+ = 5 V$ , $V_{A0, A1} = 1.4 V$ , $0.5 V$ a	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. d	Max. d	Min. d	Max. d	Unit
Dynamic Characteristics									
Turn-On Time	t <sub>on</sub>		Room	55	-	-	-	-	
rum-on rime	Lon		Full	-	-	-	-	-	
Turn-Off Time	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room	30	-	-	-	-	ne	
rum-on mile	Loff	see figure 1, 2	Full	-	-	-	-	-	ns
Break-Before-Make-Time	4		Room	36	-	-	-	=	
break-before-wake-fiffle	t <sub>BMM</sub>		Full	-	-	-	-	=	1
Charge Injection e	Q <sub>INJ</sub>	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Full	10	-	-	-	-	рС
Off-Isolation e	OIRR	f = 10 MHz, R <sub>I</sub> = 50 Ω, C <sub>I</sub> = 5 pF	Room	-58	-	-	-	-	dB
Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$1 = 10 \text{ MHz}, N_L = 50 \Omega, C_L = 5 \text{ pr}$	Room	-68	-	-	-	-	uБ
Bandwidth <sup>e</sup>	BW	$R_L = 50 \Omega$	Room	610	-	-	-	-	MHz
Total Harmonic Distortion <sup>e</sup>	THD	Signal = 1 $V_{RMS}$ , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	2.2	-	-	-	-	%
Source Off Capacitance e	C <sub>S(off)</sub>			2.1	-	-	-	=	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	f = 1 MHz	Room	8.1	-	-	-	-	pF
Power Supplies									
Davier Cumply Current			Room	0.001	-	0.5	-	0.5	
Power Supply Current	I+	$V_{IN} = 0 \text{ V, or V+}$	Full	-	-	1	-	1	
Ground Current	1	V <sub>IN</sub> = U V, UI V+	Room	-0.001	-0.5	-	-0.5	-	μA
Ground Gurrent	I <sub>GND</sub>		Full	-	-1	-	-1	-	

SPECIFICATIONS	SPECIFICATIONS											
		Test Conditions			-40 °C to 125 °C		-40 °C t	to 85 °C				
Parameter	Symbol	Unless Otherwise Specified $V+=3 V$ , $V_{A0, A1}=1.4 V$ , $0.5 V^a$	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. d	Min. <sup>d</sup>	Max. d	Unit			
Analog Switch												
Analog Signal Range e	V <sub>ANALOG</sub>		Full	-	ı	3	ı	3	V			
On-Resistance	D		Room	200	ı	245	ı	245				
On-nesistance	R <sub>DS(on)</sub>	$I_S = 1 \text{ mA}, V_D = +1.5 \text{ V}$	Full	-	-	325	-	290	Ω			
On-Resistance Match	$\Delta R_{on}$ $\Delta R_{on}$	$I_S = I IIIA, V_D = +1.5 V$	Room	5	-	6	-	6	7.2			
			Full	-	-	13	-	11				
	I <sub>S(off)</sub>		Room	± 0.01	-1	1	-1	1				
Switch Off Leakage Current		V+ = 3.3 V, V- = 0 V	Full	-	-18	18	-2	2				
(for 16 pin miniQFN)		$V_D = 1 \text{ V/3 V}, V_S = 3 \text{ V/1 V}$	Room	± 0.01	-1	1	-1	1				
	I <sub>D(off)</sub>		Full	-	-18	18	-2	2	nA			
Channel On		V+ = 3.3 V, V- = 0 V,	Room	± 0.01	-1	1	-1	1				
Leakage Current (for 16 pin miniQFN)	I <sub>D(on)</sub>	$V_{S} = V_{D} = 1 \text{ V/3 V}$	Full	-	-18	18	-2	2				
Digital Control												
Input Current, V <sub>IN</sub> Low	IL	V <sub>AX</sub> = 0.5 V	Full	0.005	-0.1	0.1	-0.1	0.1				
Input Current, V <sub>IN</sub> High	I <sub>H</sub>	V <sub>AX</sub> = 1.4 V	Full	0.005	-0.1	0.1	-0.1	0.1	μA			
Input Capacitance	C <sub>IN</sub>	f = 1 MHz	Room	3.1	-	-	-	-	рF			



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SPECIFICATIONS									
		Test Conditions			-40 °C to	o 125 °C	-40 °C		
Parameter	Symbol	Unless Otherwise Specified $V+=3~V,~V_{A0,~A1}=1.4~V,~0.5~V~a$	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. d	Min. <sup>d</sup>	Max. d	Unit
<b>Dynamic Characteristics</b>									
Enable Turn-On Time	+			96	ı	-	-	-	
Enable furn-On filme	t <sub>on</sub>		Full	-	-	-	-	-	
Enable Turn-Off Time	$R_{L} = 300 \Omega, C_{L} = 35 pF$	Room	60	-	-	-	-		
Enable Turn-Oil Time	t <sub>off</sub>	see figure 1, 2	Full	-	-	-	-	-	ns
Break-Before-Make-Time			Room	77	-	-	=	-	
break-belore-wake-Time	t <sub>BMM</sub>		Full	-	-	-	=	-	
Charge Injection <sup>e</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 0 V$	Full	6.6	-	-	-	-	рС
Off-Isolation e	OIRR	f 10 MH - D 50 O C 5 mF	Room	-57	-	-	=	-	٩D
Crosstalk e	X <sub>TALK</sub>	$f = 10 \text{ MHz}, R_L = 50 \Omega, C_L = 5 \text{ pF}$	Room	-69	-	-	-	-	dB
Bandwidth <sup>e</sup>	BW	$R_L = 50 \Omega$	Room	525	-	-	=	-	MHz
Total Harmonic Distortion <sup>e</sup>	THD	Signal = 1 $V_{RMS}$ , 20 Hz to 20 kHz, $R_L = 600 \Omega$	Room	2.2	-	-	-	-	%
Source Off Capacitance e	C <sub>S(off)</sub>			2.1	-	-	-	-	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	f = 1 MHz	Room	8.3	-	-	-	-	pF
Power Supplies									
Dower Cupply Current	I+		Room	0.001	-	0.5	-	0.5	
Power Supply Current	1+	V = 0 V or V	Full	-	-	1	-	1	
Ground Current		$V_{IN} = 0 \text{ V, or V+}$	Room	-0.001	-0.5	-	-0.5	-	μA
Ground Current	I <sub>GND</sub>		Full	-	-1	-	-1	-	

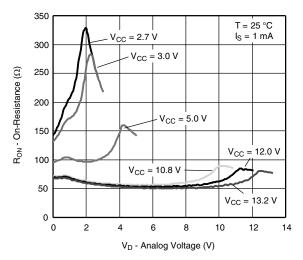
### Notes

- a.  $V_{IN}$  = input voltage to perform proper function.
- b. Room = 25 °C, Full = as determined by the operating temperature.
- c. Typical value are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.

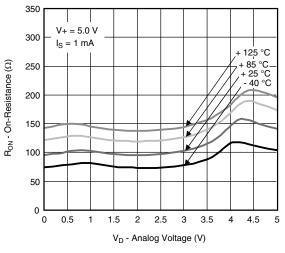
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



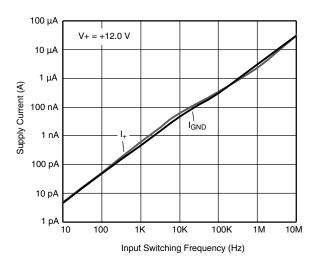
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



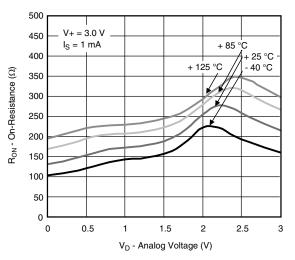
On-Resistance vs. Single Supply Voltage



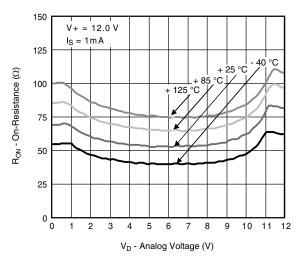
On-Resistance vs. Analog Voltage and Temperature



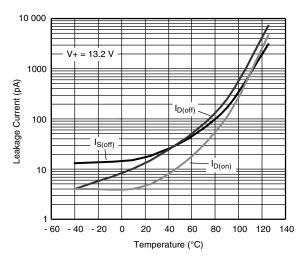
Supply Current vs. Input Switching Frequency



On-Resistance vs. Analog Voltage and Temperature



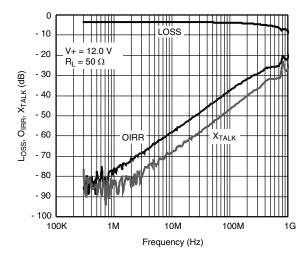
On-Resistance vs. Analog Voltage and Temperature



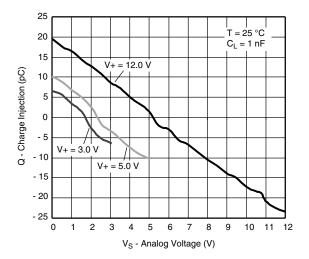
Leakage Current vs. Temperature



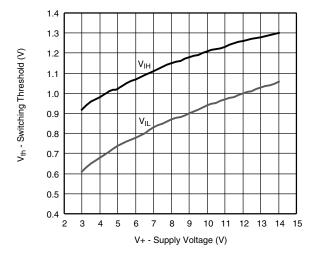
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Charge Injection vs. Analog voltage



Switching Threshold vs. Supply Voltage

### **TEST CIRCUITS**

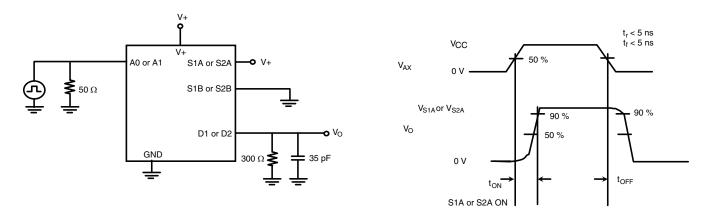


Figure 1. Enable Switching Time

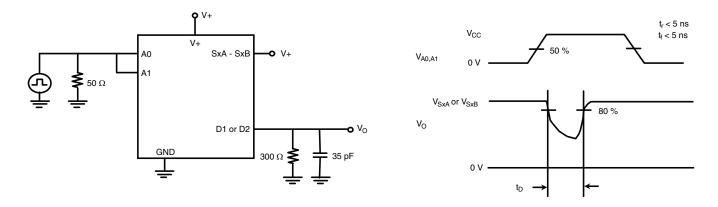


Figure 2. Break-Before-Make

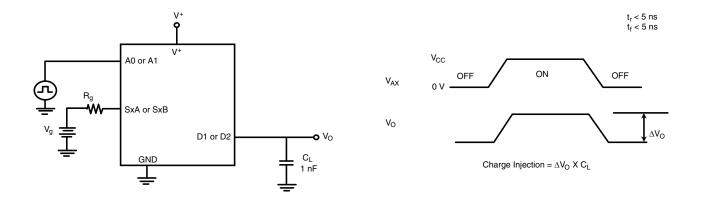


Figure 3. Charge Injection



### **TEST CIRCUITS**

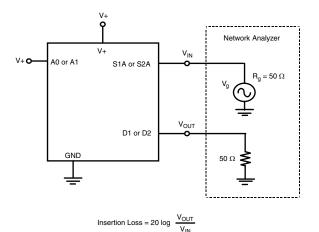


Figure 4. Insertion Loss

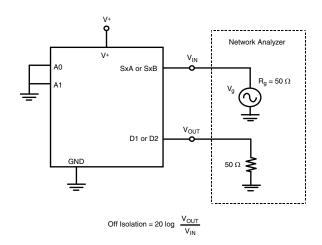


Figure 5. Off-Isolation

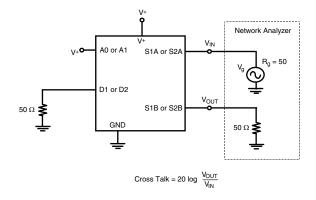


Figure 6. Crosstalk

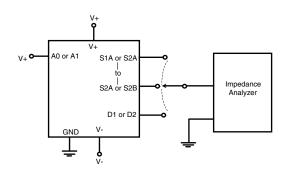
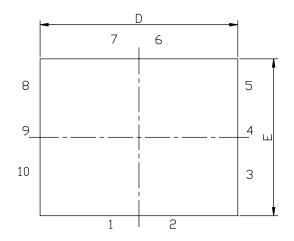


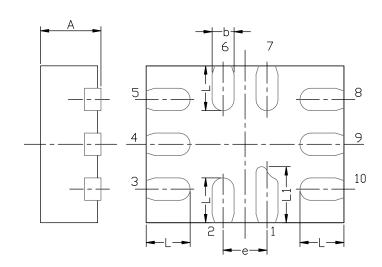
Figure 7. Source/Drain Capacitance

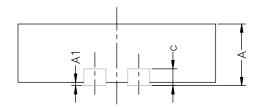
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# MINI QFN-10L CASE OUTLINE







DIM		MILLIMETERS			INCHES		
DIM	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.45	0.55	0.60	0.0177	0.0217	0.0236	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С		0.150 or 0.127 REF <sup>(</sup>	1)	(	0.006 or 0.005 REF <sup>(1</sup>	)	
D	1.70	1.80	1.90	0.067	0.071	0.075	
E	1.30	1.40	1.50	0.051	0.055	0.059	
е		0.40 BSC		0.016 BSC			
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217	

#### Note

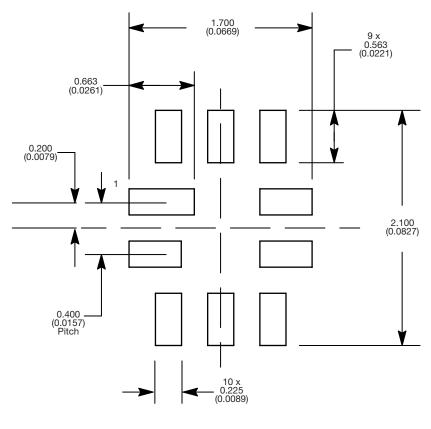
ECN T16-0163-Rev. B, 16-May-16 DWG: 5957

<sup>(1)</sup> The dimension depends on the leadframe that assembly house used.



Vishay Siliconix

### **RECOMMENDED MINIMUM PADS FOR MINI QFN 10L**



Mounting Footprint Dimensions in mm (inch)



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